

## N-Channel 100-V (D-S) MOSFET

PRODUCT SUMMARY		
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
100	0.062 at $V_{GS} = 10$ V	5.4
	0.084 at $V_{GS} = 6$ V	4.6

### FEATURES

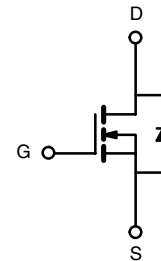
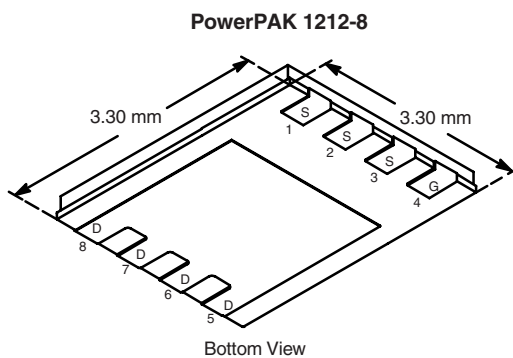
- Halogen-free Option Available
- TrenchFET<sup>®</sup> Power MOSFET
- New Low Thermal Resistance
- PowerPAK<sup>®</sup> 1212-8 Package with Low 1.07 mm Profile
- PWM Optimized



**RoHS**  
COMPLIANT

### APPLICATIONS

- Primary Side Switch
- In-Rush Current Limiter



N-Channel MOSFET

**Ordering Information:** Si7810DN-T1-E3 (Lead (Pb)-free)  
Si7810DN-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted					
Parameter	Symbol	10 s	Steady State	Unit	
Drain-Source Voltage	$V_{DS}$	100		V	
Gate-Source Voltage	$V_{GS}$	$\pm 20$			
Continuous Drain Current ( $T_J = 150$ °C) <sup>a</sup>	$I_D$	$T_A = 25$ °C	5.4	3.4	A
		$T_A = 70$ °C	4.3	2.8	
Pulsed Drain Current	$I_{DM}$	20			
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	3.2	1.3	A	
Single Avalanche Current	$I_{AS}$	19			
Single Avalanche Energy (Duty Cycle 1 %)		$E_{AS}$	18		
Maximum Power Dissipation <sup>a</sup>	$P_D$	$T_A = 25$ °C	3.8	1.5	W
		$T_A = 70$ °C	2.0	0.8	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150		°C	
Soldering Recommendations <sup>b,c</sup>		260			

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	$t \leq 10$ s	$R_{thJA}$	26	33	°C/W
	Steady State		65	81	
Maximum Junction-to-Case (Drain)	Steady State	$R_{thJC}$	1.9	2.4	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. See Solder Profile (<http://www.vishay.com/ppg?73257>). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2		4.5	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			5	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	20			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 5.4\text{ A}$		0.052	0.062	$\Omega$
		$V_{GS} = 6\text{ V}, I_D = 4.6\text{ A}$		0.070	0.084	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 5.4\text{ A}$		12		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 3.2\text{ A}, V_{GS} = 0\text{ V}$		0.78	1.2	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = 50\text{ V}, V_{GS} = 10\text{ V}, I_D = 5.4\text{ A}$		13.5	17	nC
Gate-Source Charge	$Q_{gs}$			3		
Gate-Drain Charge	$Q_{gd}$			4.6		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 50\text{ V}, R_L = 50\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_G = 6\text{ }\Omega$		10	15	ns
Rise Time	$t_r$			15	25	
Turn-Off Delay Time	$t_{d(off)}$			20	30	
Fall Time	$t_f$			15	25	
Source-Drain Reverse Recovery Time	$t_{rr}$	$I_F = 3.2\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		45	90	

Notes:

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## TYPICAL CHARACTERISTICS $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted

